

MAR 04 2005

REPLY UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER 2811

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: Bruley, *et al.* Conf. #: 2127  
Serial No.: 10/605,128 Art Unit: 2814  
Filed: 09/10/2003 Docket No.: FIS920030230US1 (IBMF-0025)  
Title: CAPACITOR AND FABRICATION  
METHOD USING ULTRA-HIGH  
VACUUM CVD OF SILICON NITRIDE Examiner: Weiss, Howard

## COMMISSIONER FOR PATENTS

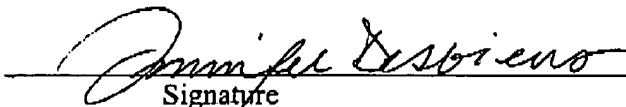
DESTINATION FACSIMILE NUMBER: 703-872-9306

Transmitted herewith is: After-Final Amendment in 7 pages  
in the above identified application.

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Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AFTER-FINAL AMENDMENT**

Sir:

**I. INTRODUCTORY COMMENTS**

In response to the final Office Action of January 5, 2005, please amend the above-referenced patent application as follows.

10/605,128

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